ABSTRACT OF THE DISCLOSURE

In anodic bonding between a conductor or semiconductor and glass, in order to attain good adhesion at a lower bonding temperature than usual and improve the toughness at its boundary to obtain higher reliability for a bonded portion even in a case where bonded members are warped or dust is present at the bonding boundary, a soft metal film is formed on the surface of a conductor or semiconductor on which an active metal film having high reactivity with oxygen is formed, whereby a warp or dust, if any, can be absorbed by the deformation of the soft metal film, thereby to improve the adhesion at the boundary. Adhesion at the bonding boundary is improved even at a low bonding temperature of, e.g., about 200°C. Further, the toughness at the bonding boundary can be improved to increase reliability by roughening the bonded surface on the side of the glass.